



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#16/A
OK
4/28/03

In re Application of

Koike et al.

Serial No.: 09/725,496

Group Art Unit: 2811

Filed: November 30, 2000

Examiner: Crane, Sara W.

For: LIGHT-EMITTING DEVICE USING GROUP III NITRIDE GROUP COMPOUND
SEMICONDUCTOR

Honorable Commissioner of Patents
Washington, D.C. 20231

AMENDMENT UNDER 37 C.F.R. §1.111

Sir:

In response to the Office Action dated December 19, 2002, please amend the above-identified application as follows:

IN THE CLAIMS:

Please cancel claims 3-4, 6, 10 and 12 without prejudice or disclaimer.

Please amend the claims to read as follows:

- Sub
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Q1
1. (Amended) A light-emitting semiconductor device comprising:
a substrate;
plural semiconductor layers which are made of group III nitride group compound semiconductor formed on said substrate; and
an active layer comprising at least a quantum well layer which satisfies the formula $Al_{1-x}In_xN$, where a composition ratio x of indium (In) is in a range of $0.1 \leq x \leq 1$.
 2. (Amended) A light-emitting semiconductor device using a group III nitride group compound semiconductor according to claim 1, said active layer comprising a multiple quantum well structure in which said quantum well layer which satisfies said formula and a quantum barrier layer which satisfies the formula $Al_{1-z-y}Ga_yIn_zN$ ($0 \leq y \leq 1$, $0 \leq z < 1$, $0 \leq z+y \leq 1$) are laminated together alternately.